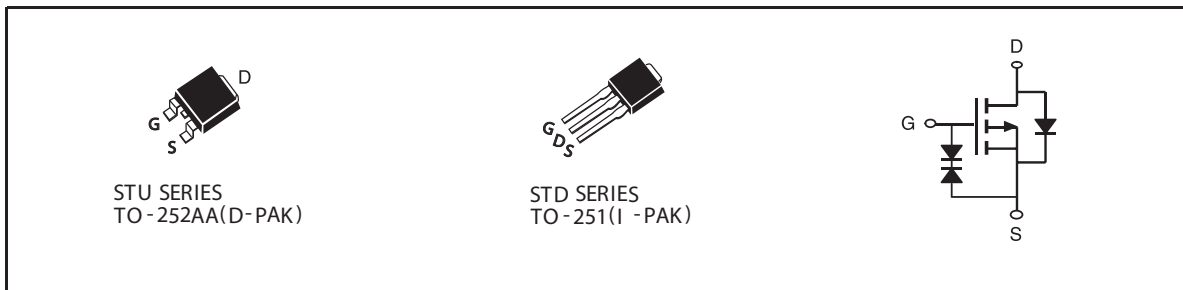


**P-Channel Logic Level Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
-30V	-53A	9.5 @ V _{GS} =-10V
		14 @ V _{GS} =-4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.

**ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	-30	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^a	T _C =25°C	-53
		T _C =70°C	-42
I _{DM}	-Pulsed ^b	-160	A
P _D	Maximum Power Dissipation ^a	T _C =25°C	42
		T _C =70°C	27
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case ^a	3	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient ^a	50	°C/W

STU/D307S

Ver 1.0

ELECTRICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-24V, V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} =0V			±10	uA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-1	-1.8	-3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =-10V, I _D =-26.5A		7.5	9.5	m ohm
		V _{GS} =-4.5V, I _D =-21A		10.5	14	m ohm
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-26.5A		52		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V f=1.0MHz		3100		pF
C _{OSS}	Output Capacitance			850		pF
C _{RSS}	Reverse Transfer Capacitance			400		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =-15V I _D =-1.0A V _{GS} =-10V R _{GEN} = 6 ohm		45		ns
t _r	Rise Time			85		ns
t _{D(OFF)}	Turn-Off Delay Time			340		ns
t _f	Fall Time			150		ns
Q _g	Total Gate Charge	V _{DS} =-15V, I _D =-25A, V _{GS} =-10V		75		nC
		V _{DS} =-15V, I _D =-25A, V _{GS} =-4.5V		35		nC
Q _{gs}	Gate-Source Charge	V _{DS} =-15V, I _D =-25A,		8		nC
Q _{gd}	Gate-Drain Charge	V _{GS} =-10V		22		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
I _s	Maximum Continuous Drain-Source Forward Current				-12	A
V _{SD}	Diode Forward Voltage ^b	V _{GS} =0V, I _s = -12A		-0.8	-1.3	V
Notes a.Surface Mounted on FR4 Board, t ≤ 10sec. b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%. c.Guaranteed by design, not subject to production testing.						

Jan,29,2010

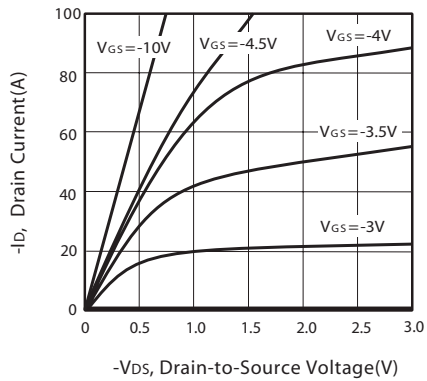


Figure 1. Output Characteristics

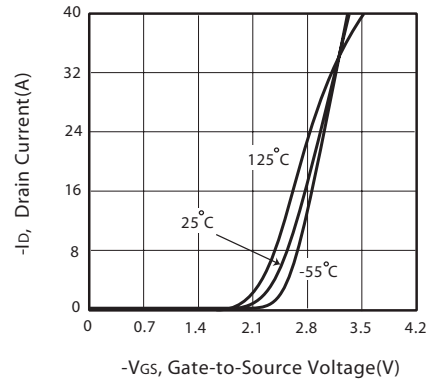


Figure 2. Transfer Characteristics

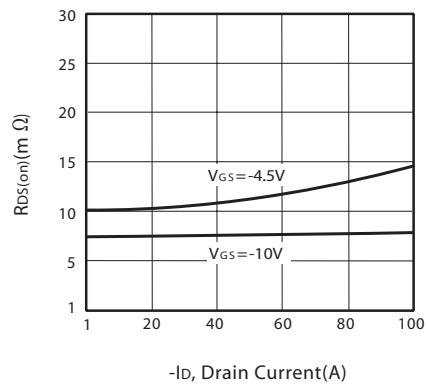


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

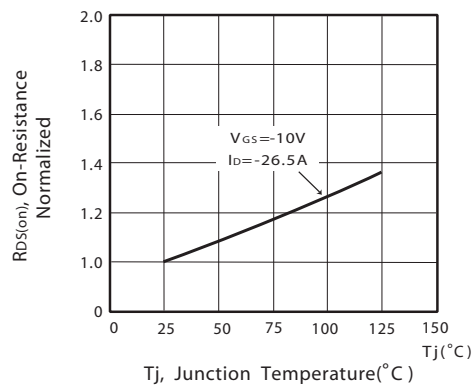


Figure 4. On-Resistance Variation with Drain Current and Temperature

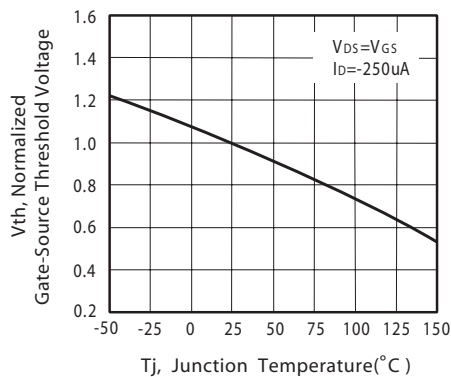


Figure 5. Gate Threshold Variation with Temperature

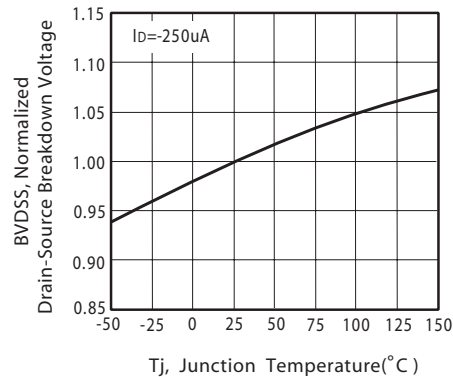


Figure 6. Breakdown Voltage Variation with Temperature

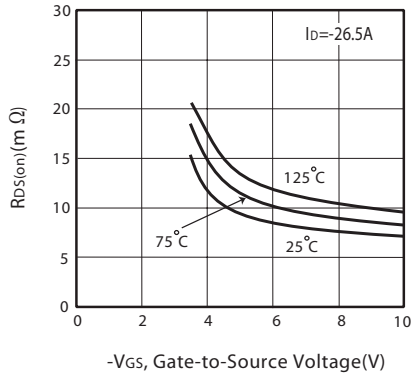


Figure 7. On-Resistance vs. Gate-Source Voltage

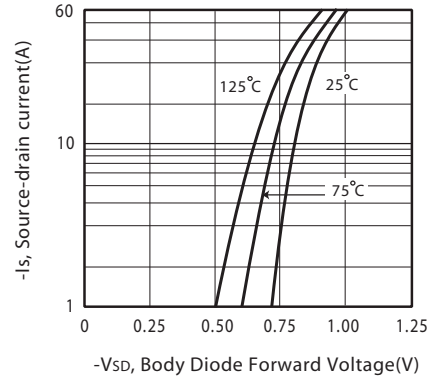


Figure 8. Body Diode Forward Voltage Variation with Source Current

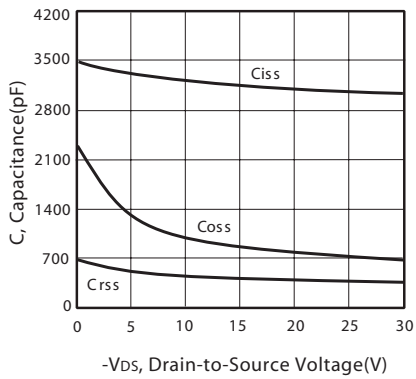


Figure 9. Capacitance

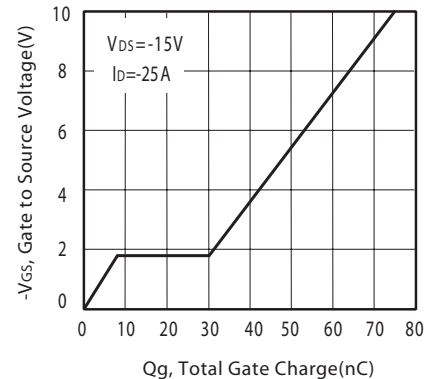


Figure 10. Gate Charge

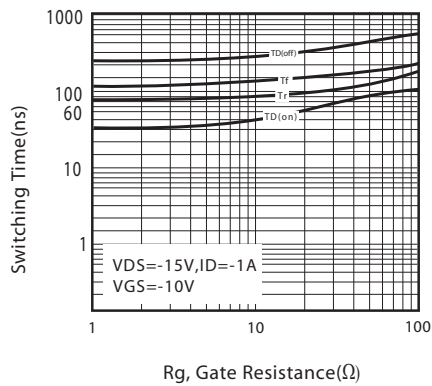


Figure 11. switching characteristics

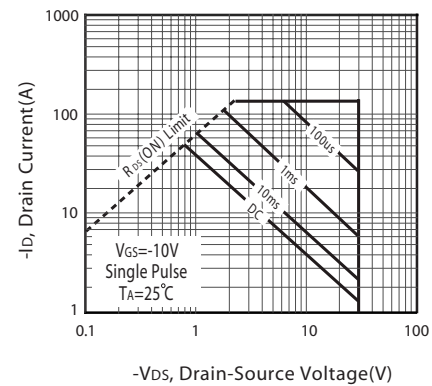


Figure 12. Maximum Safe Operating Area

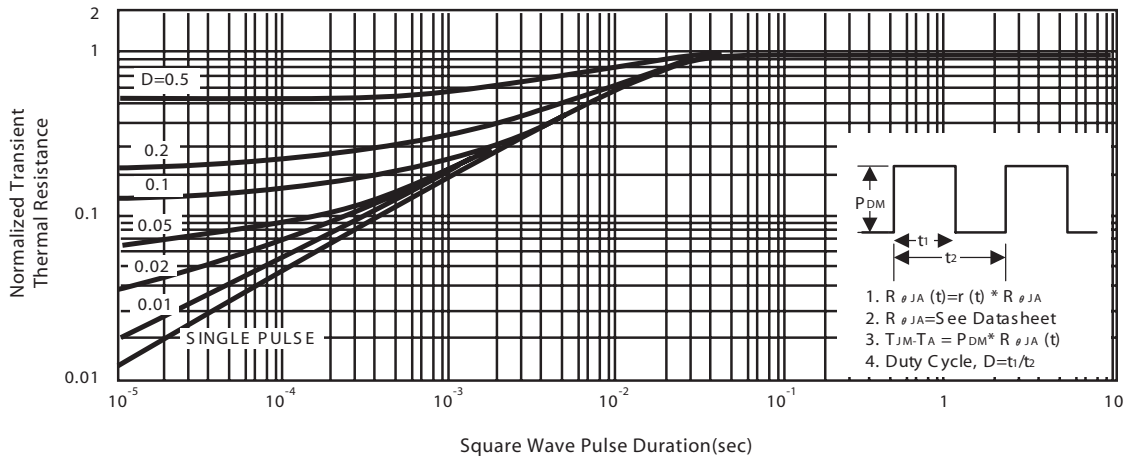
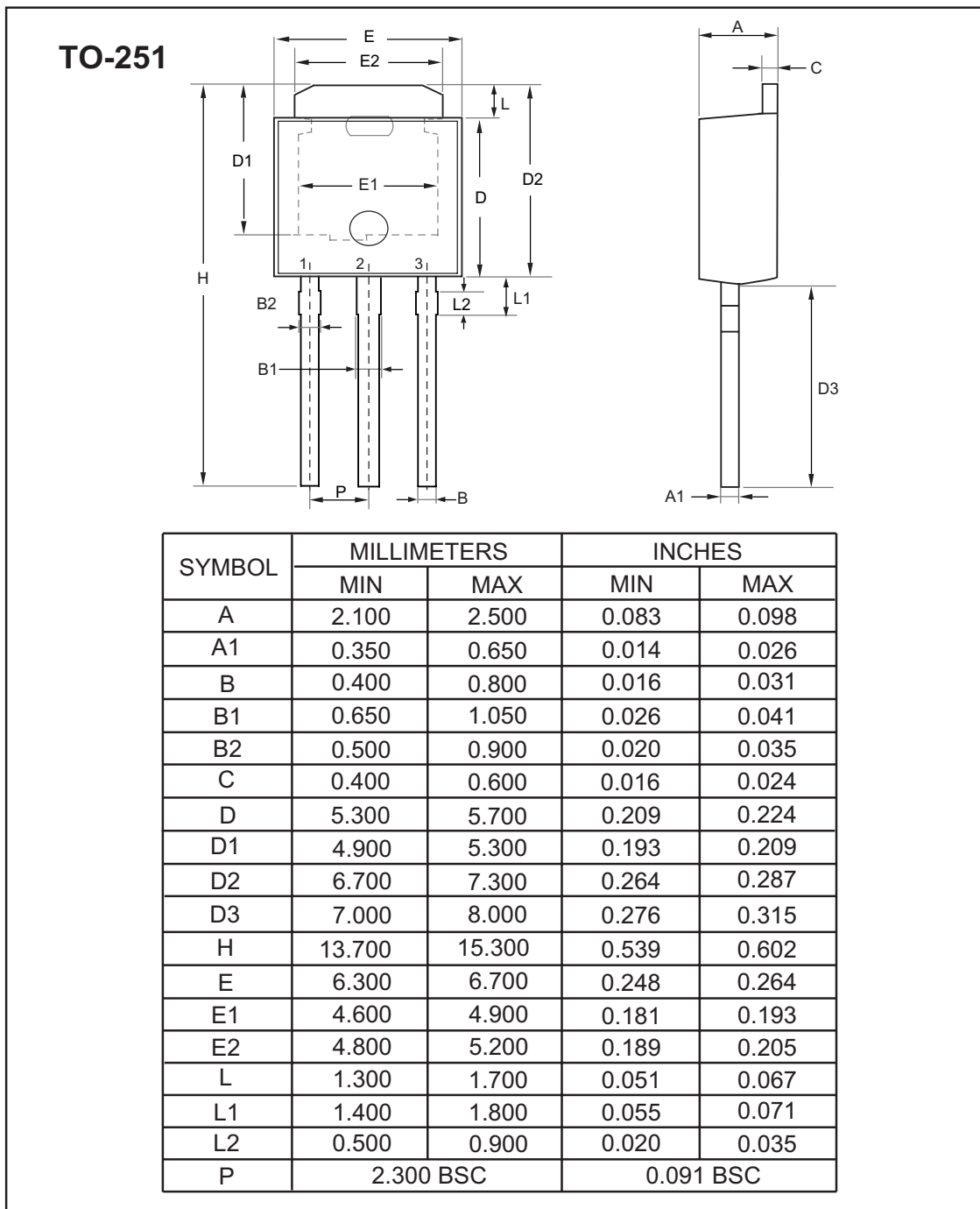
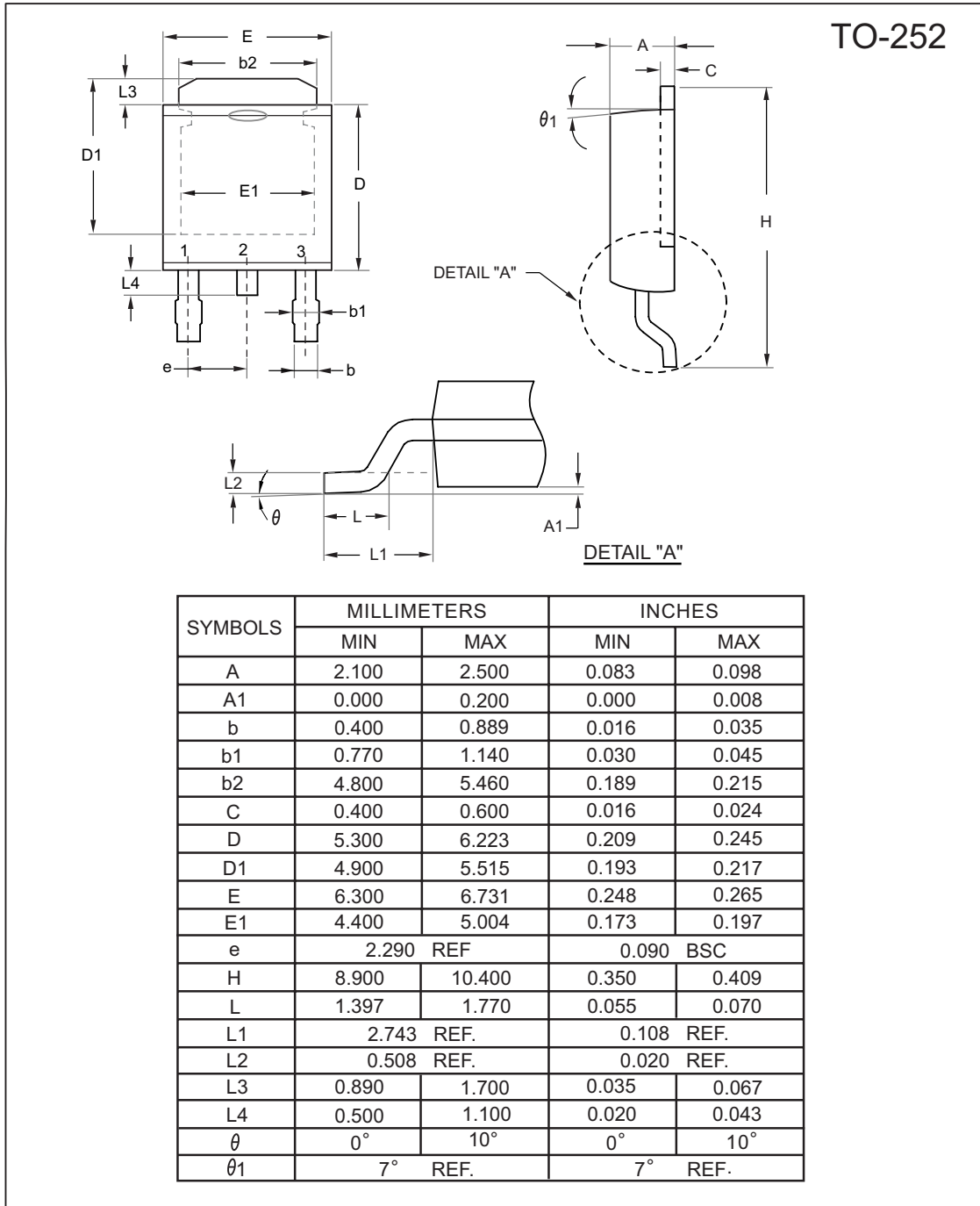


Figure 13. Normalized Thermal Transient Impedance Curve

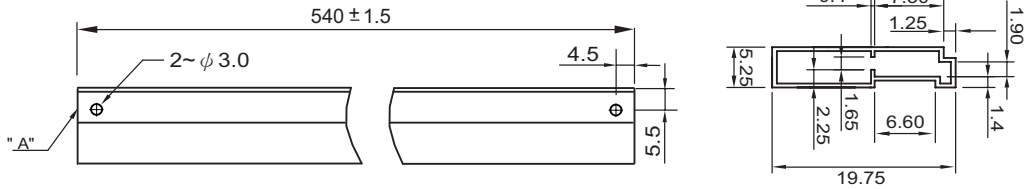
PACKAGE OUTLINE DIMENSIONS



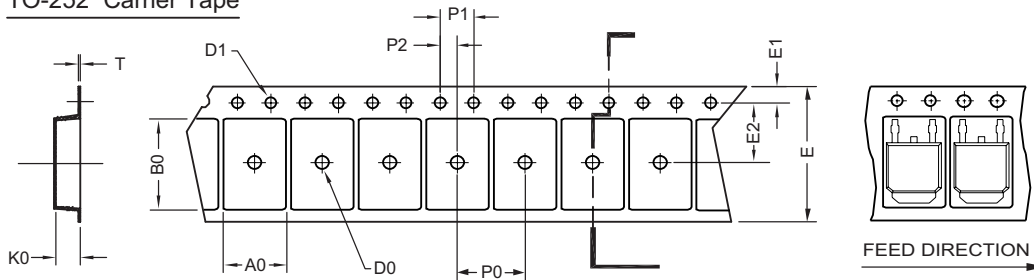


TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



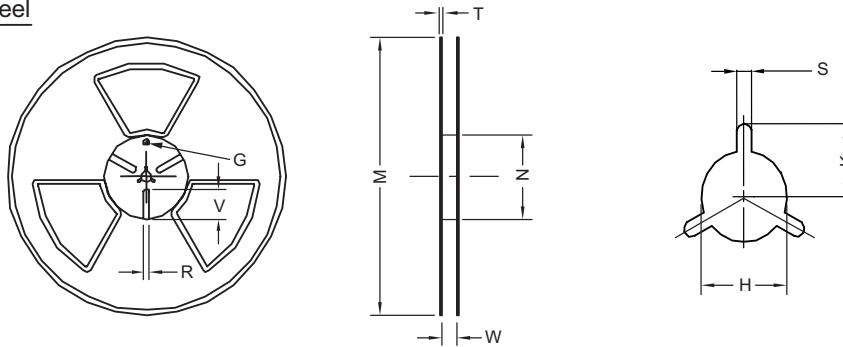
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ2	φ1.5 +0.1 -0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---